

isc Silicon NPN Power Transistor

ISC1205

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DESCRIPTION

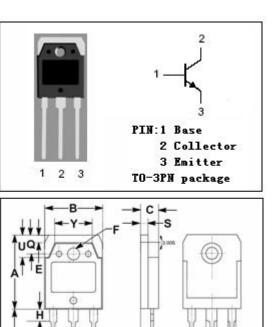
- · High Breakdown Voltage-
- : V_{(BR)CBO}= 1500V(Min)
- High Switching Speed
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

 Ultrahigh-definition CRT display horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--|---------|------|--|
| V _{сво} | Collector-Base Voltage | 1500 | V | |
| V _{CEO} | Collector-Emitter Voltage | 800 | V | |
| V _{EBO} | Emitter-Base Voltage | 6 | V | |
| lc | Collector Current-Continuous | 15 | A | |
| I _{CP} | Collector Current-Peak | 25 | A | |
| Pc | Collector Power Dissipation @ T_c =25 °C | 150 | W | |
| TJ | Junction Temperature | 150 | °C | |
| T _{stg} | Storage Temperature Range | -55~150 | Ĉ | |



| -Y | m | m |
|------------------|-------|-------|
| DIM | MIN | MAX |
| Α | 19.60 | 20.10 |
| | 15.50 | 15.70 |
| B C D E | 4.70 | 4.90 |
| D | 0.90 | 1.10 |
| E | 1.90 | 2.10 |
| F | 3.40 | 3.60 |
| G | 2.90 | 3.20 |
| | 3.20 | 3.40 |
| H J | 0.595 | 0.605 |
| K | 20.00 | 20.70 |
| L | 1.90 | 2.20 |
| N | 10.89 | 10.91 |
| Q | 4.90 | 5.10 |
| R | 3.35 | 3.45 |
| S | 1.995 | 2.100 |
| U | 5.90 | 6.10 |
| Y | 9.90 | 10.10 |

isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

$T_{c}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | МАХ | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 30mA; I _B = 0 | 800 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 8A; I _B = 2A | | | 5.0 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 8A; I _B = 2A | | | 1.5 | V |
| I _{СВО} | Collector Cutoff Current | V _{CB} = 800V ; I _E = 0 | | | 10 | μA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 4V ; I _C = 0 | | | 0.1 | mA |
| h _{FE-1} | DC current gain | I _C = 1A ; V _{CE} = 5V | 20 | | 30 | |
| h _{FE-2} | DC current gain | I _C = 8A ; V _{CE} = 5V | 4 | | 8 | |

Switching times

| | | _ | | | | |
|------------------|--------------|---|---|------|-----|------------|
| t _{stg} | Storage Time | | I _C = 6A , I _{B1} = 1.2A; I _{B2} = -2.4A R _L = 50 Ω ; V _{CC} = 200V | | 3.0 | μ S |
| t _f | Fall Time | | | | 0.2 | μ S |

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